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Sir:

In response to the Office Action mailed May 9, 2002, please amend the above-identified application as follows:

IN THE TITLE:

Please replace the title with the following new title:

METHOD OF MANUFACTURING A CIRCUIT BOARD HAVING
SIMULTANEOUSLY AND UNITARILY FORMED WIRING PATTERNS AND
PROTRUSIONS

IN THE CLAIMS:

Please amend claims 24-26 and 29-31 as follows:

24. (Twice Amended) A method of manufacturing a circuit board comprising a plurality of wiring patterns each extending across a surface of an insulating substrate for connecting at least two locations on the substrate, and a plurality of protrusions located at desired locations on the wiring patterns, comprising:

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simultaneously and unitarily forming the wiring patterns and the protrusions, and modifying the protrusions to have substantially equal heights.

25. (Amended) The method of manufacturing the circuit board as defined in Claim 24, wherein the wiring patterns and the protrusions are made of a same conductive sintered material.

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26. (Twice Amended) The method of manufacturing the circuit board as defined in Claim 25, wherein forming the wiring patterns and the protrusions of the same conductive sintered material comprises:

forming a first groove on a film, the first groove having a bottom surface;

forming a second groove at a predetermined location in the first groove;

filling sintering conductive material into the first and the second grooves;

transferring the filled sintering conductive material onto the substrate; and

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sintering the transferred conductive material.

29. (Twice Amended) A method of manufacturing a semiconductor device comprising the steps of:

simultaneously and unitarily forming a first plurality of wiring patterns and a second plurality of protrusions located at desired locations on the wiring patterns on a an insulating substrate, the protrusions having substantially equal heights, the wiring patterns each extending across a surface of the substrate for connecting at least two locations on the substrate;

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modifying the protrusions to have substantially equal heights;
and

coupling electrically the protrusions to electrodes located on a semiconductor chip component.

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30. (Amended) The method of manufacturing the semiconductor device as defined in Claim 29, wherein the wiring patterns and the protrusions are made of a same conductive sintered material.

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31. (Twice Amended) The method of manufacturing the semiconductor device as defined in Claim 30, wherein forming the wiring patterns and the protrusions of the same conductive material comprises:

forming a first groove on a film, the first groove having a bottom surface;

forming a second groove at a predetermined location in the first groove;

filling sintering conductive material into the first and the second grooves;

transferring the filled sintering conductive material onto the substrate; and

sintering the transferred conductive material.

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